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(71) Applicant: MICRON TECHNOLOGY, INC. [US/US];
8000 South Federal Way, Boise, ID 83716 (US).

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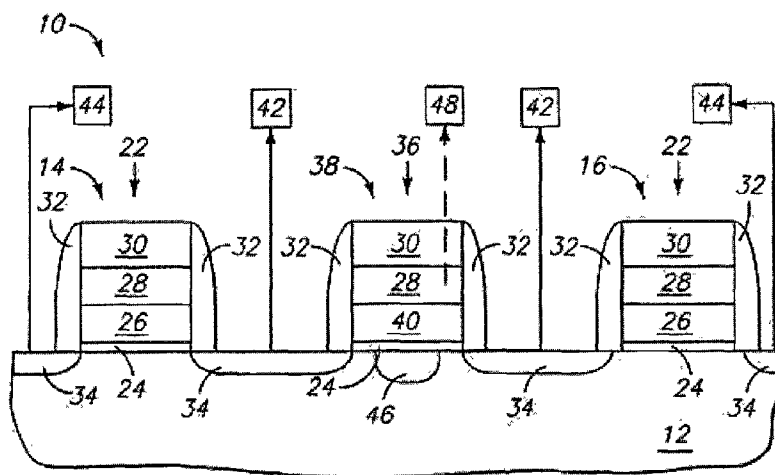
(72) Inventor: LUAN, Tran, C.; 1125 W. Sandy, Ct., Meridian,
ID 83642 (US).

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(74) Agents: TAYLOR, Jennifer, J. et al.; Wells St. John P.S.,
601 West First Ave, Spokane, WA 99201 (US).

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(54) Title: SEMICONDUCTOR CONSTRUCTIONS WITH GATED ISOLATION REGIONS HAVING INDIUM-DOPED SUB-REGIONS



(57) Abstract: The invention includes a semiconductor construction wherein gate structures are separated by isolation regions that are provided with an indium-doped pocket and a covering gate. The invention also includes a semiconductor construction having a pair of channel regions that have sub-regions doped with indium and surrounded by boron. A pair of transistor constructions are located over the channel regions and are separated by an isolation region. The transistors have gates that are wider than the underlying sub-regions. The invention also includes a semiconductor construction that has transistor constructions with insulative spacers along gate sidewalls. Each transistor construction is between a pair source/drain regions that extend beneath the spacers. A source/drain extension extends the source/drain region farther beneath the transistor constructions on only one side of each of the transistor constructions. The invention also includes methods of forming semiconductor constructions.

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